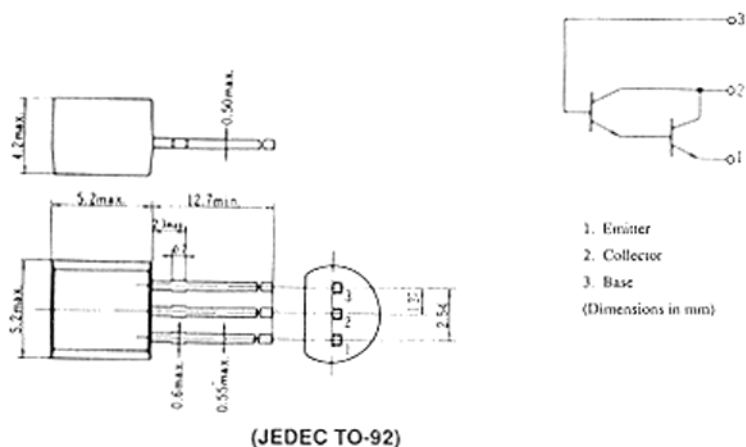


## 2SC1472 (K)

SILICON NPN EPITAXIAL PLANAR

HIGH GAIN AMPLIFIER

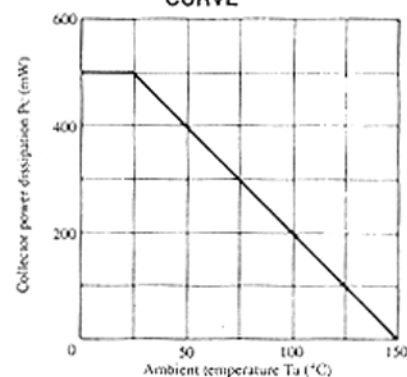


1. Emitter
  2. Collector
  3. Base
- (Dimensions in mm)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC1472 (K)	Unit
Collector to base voltage	V <sub>CB0</sub>	40	V
Collector to emitter voltage	V <sub>CE0</sub>	30	V
Emitter to base voltage	V <sub>EB0</sub>	10	V
Collector current	I <sub>C</sub>	300	mA
Collector peak current	i <sub>C(peak)</sub>	500	mA
Collector power dissipation	P <sub>C</sub>	500	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### MAXIMUM COLLECTOR DISSIPATION CURVE



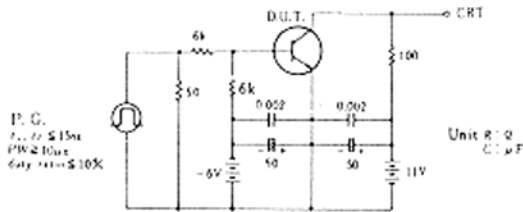
### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	30	—	—	V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0	—	—	100	nA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> = 10V, I <sub>C</sub> = 0	—	—	100	nA
DC current transfer ratio	h <sub>FE1</sub> *	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V	2,000	—	100,000	
	h <sub>FE2</sub> *	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V (Pulse Test)	3,000	—	—	
	h <sub>FE3</sub> *	I <sub>C</sub> = 400mA, V <sub>CE</sub> = 5V (Pulse Test)	3,000	—	—	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0.1mA	—	—	1.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0.1mA	—	—	2.0	V
Gain bandwidth product	f <sub>T</sub>	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V	50	—	—	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, f = 1MHz	—	—	10	pF
Turn on time	t <sub>on</sub>	V <sub>CC</sub> = 11V	—	60	—	ns
Turn off time	t <sub>off</sub>	I <sub>C</sub> = 100I <sub>B1</sub> = -100I <sub>B2</sub> = -100mA	—	800	—	ns
Storage time	t <sub>stg</sub>		—	350	—	ns

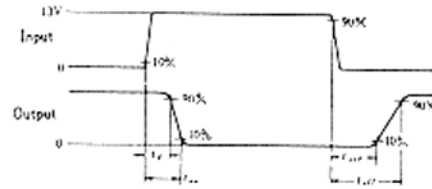
\* The 2SC1472 (K) is grouped by h<sub>FE</sub> as follows.

	A	B
h <sub>FE1</sub>	2,000 to 100,000	5,000 to 100,000
h <sub>FE2</sub>	3,000 min	10,000 min
h <sub>FE3</sub>	3,000 min	10,000 min

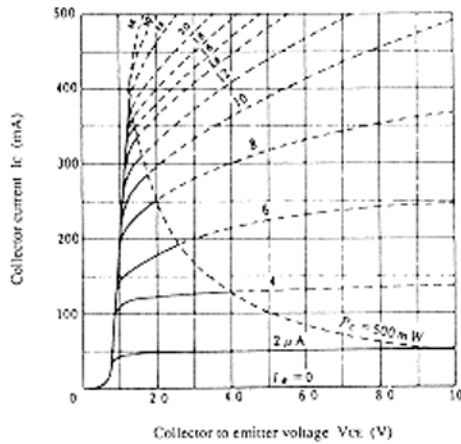
### SWITCHING TIME TEST CIRCUIT



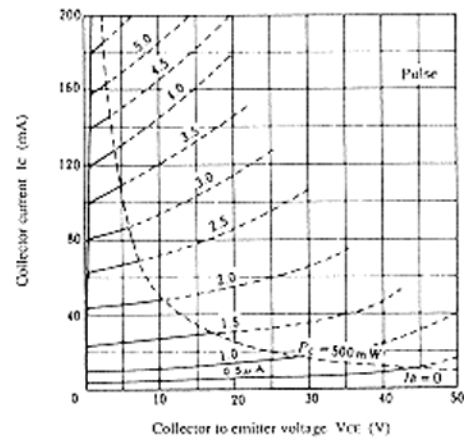
### RESPONSE WAVEFORM



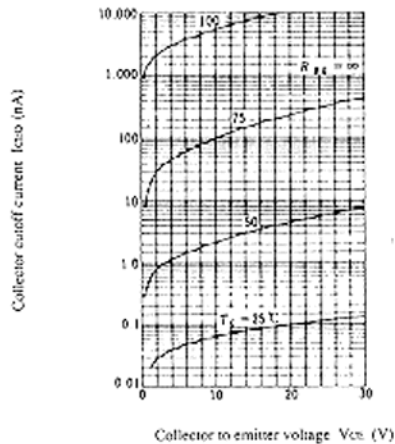
### TYPICAL OUTPUT CHARACTERISTICS



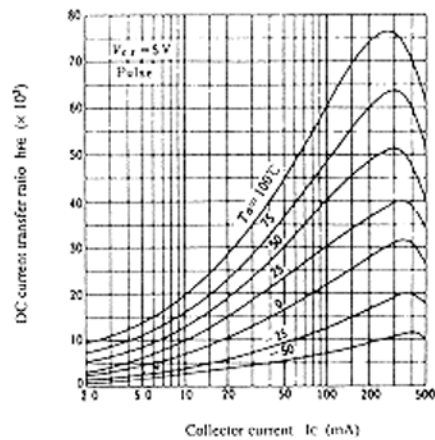
### TYPICAL OUTPUT CHARACTERISTICS



### COLLECTOR CUTOFF CURRENT VS. COLLECTOR TO EMITTER VOLTAGE

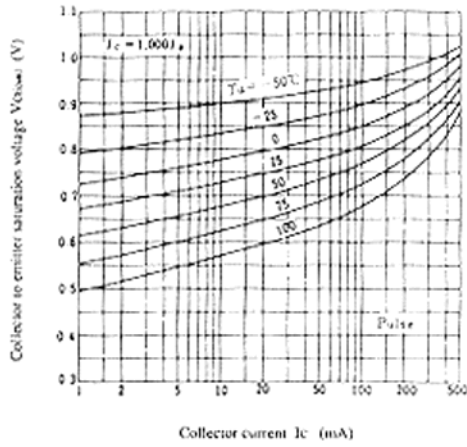


### DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT

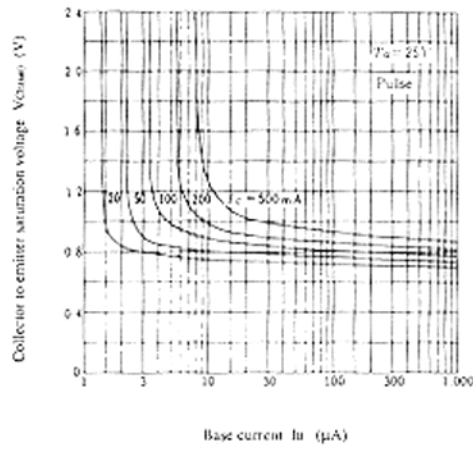


## 2SC1472(K)

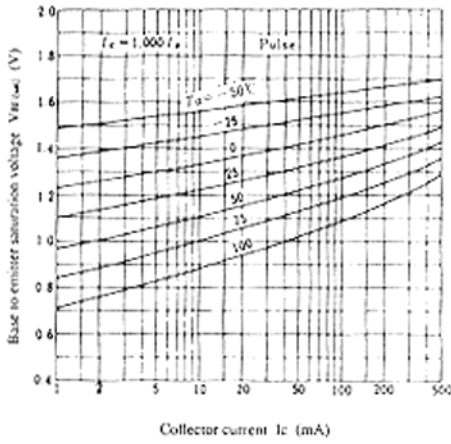
### COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



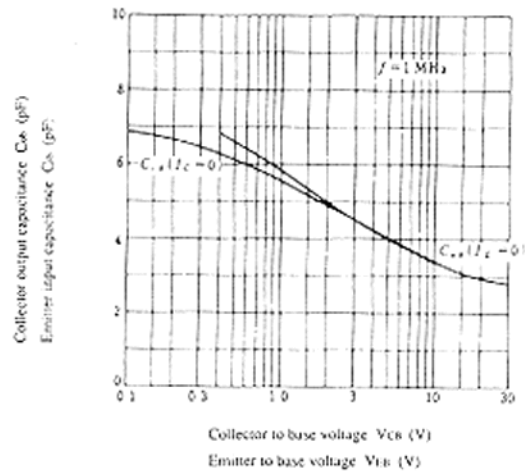
### COLLECTOR TO EMITTER SATURATION VOLTAGE VS. BASE CURRENT



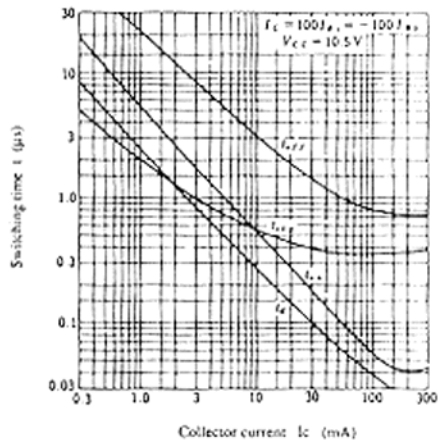
### BASE TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



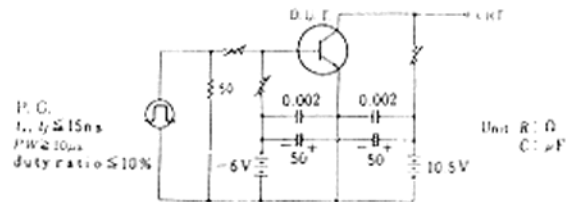
### INPUT AND OUTPUT CAPACITANCE VS. VOLTAGE



### SWITCHING TIME VS. COLLECTOR CURRENT



### SWITCHING TIME TEST CIRCUIT



### RESPONSE WAVEFORM

